



Dual P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
- 30	$0.025 \text{ at V}_{GS} = -10 \text{ V}$	- 7.1		
	0.041 at V _{GS} = - 4.5 V	- 5.5		

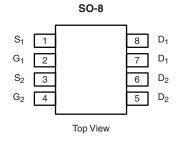
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

ROHS COMPLIANT HALOGEN FREE

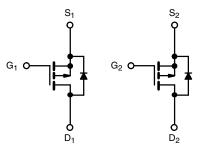
APPLICATIONS

- Load Switches
 - Notebook PCs
 - Desktop PCs
 - Game Stations



Ordering Information: Si4925BDY-T1-E3 (Lead (Pb)-free)

Si4925BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	$T_A = 25 ^{\circ}C$, unle	ss otherwise n	noted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 30		V	
Gate-Source Voltage		V _{GS}	± 20			
Continuous Dunin Comment /T 150 00\d	T _A = 25 °C	- I _D	- 7.1	- 5.3		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 5.7	- 4.3	Δ.	
Pulsed Drain Current		I _{DM}	- 40		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.7	- 0.9		
W	T _A = 25 °C	В	2.0	1.1	W	
Maximum Power Dissipation ^a	T _A = 70 °C	- P _D	1.3	0.7	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian Innation to Ambient	t ≤ 10 s	- R _{thJA}	50	62.5	°C/W
Maximum Junction-to-Ambient ^a	Steady State		85	110	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	30	40]

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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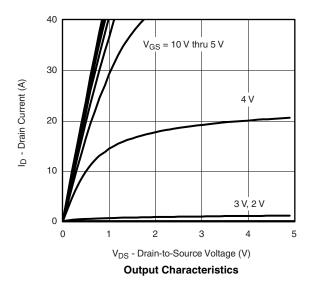
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V	GS = 0 V		- 1	μΑ	
		V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C			- 25		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 40			Α	
	В	V _{GS} = - 10 V, I _D = - 7.1 A		0.020	0.025		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 5.5 A		0.033	0.041	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 7.1 A		20		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 1.7 A, V _{GS} = 0 V		- 0.8	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			33	50		
Gate-Source Charge	Q_{gs}	V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 7.1 A		5.4		nC	
Gate-Drain Charge	Q_{gd}			8.9			
Turn-On Delay Time	t _{d(on)}			9	15		
Rise Time	t _r	$ \begin{array}{c c} t_r & V_{DD} = \text{- 15 V, R}_L = \text{15 } \Omega \\ \hline t_{d(off)} & I_D \cong \text{- 1 A, V}_{GEN} = \text{- 10 V, R}_g = \text{6 } \Omega \\ \end{array} $		12	20	ns	
Turn-Off Delay Time	t _{d(off)}			60	90		
Fall Time	t _f			34	50		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.7 A, dl/dt = 100 A/μs		30	60		

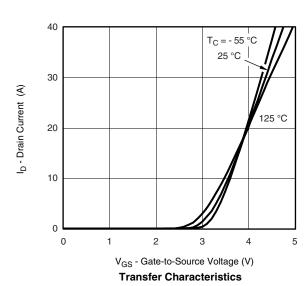
Notes:

- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



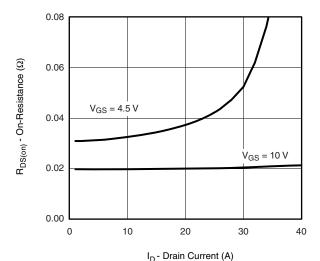




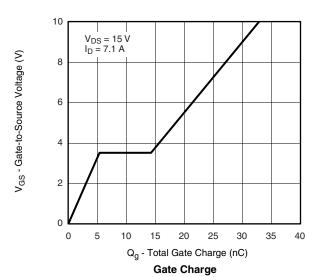


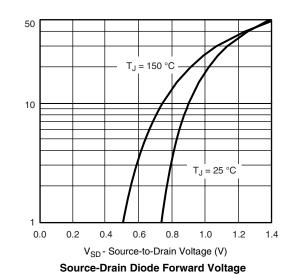


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Drain Current

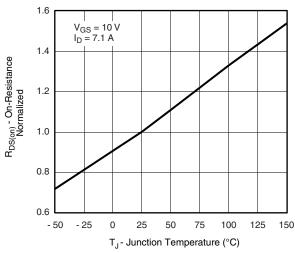




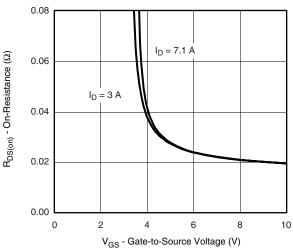
2500 2000 C_{iss} C - Capacitance (pF) 1500 1000 Coss 500 $\mathsf{C}_{\mathsf{rss}}$ 0 0 6 12 18 24 30

V_{DS} - Drain-to-Source Voltage (V)

Capacitance



On-Resistance vs. Junction Temperature



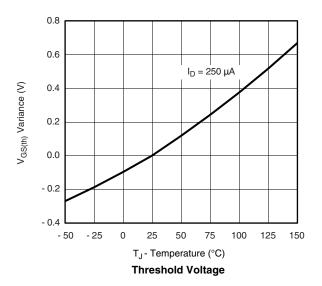
On-Resistance vs. Gate-to-Source Voltage

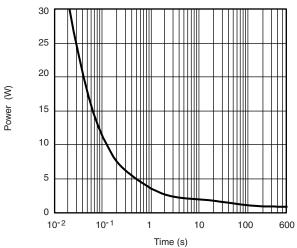
I_S - Source Current (A)

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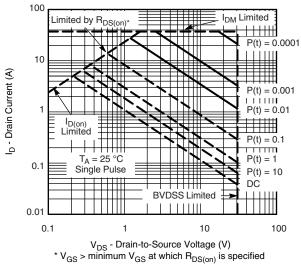
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

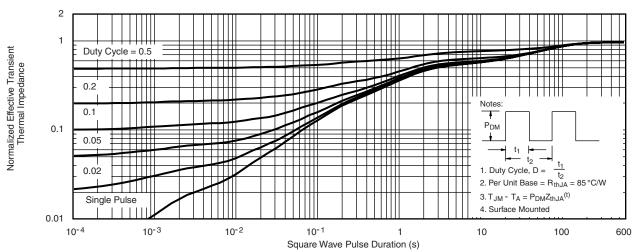




Single Pulse Power



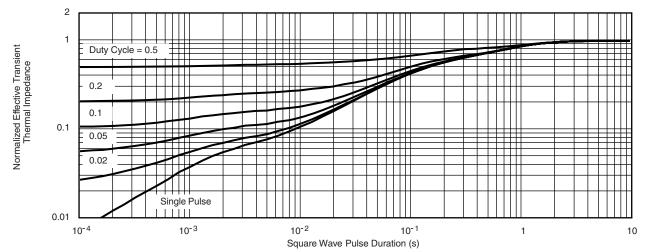
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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